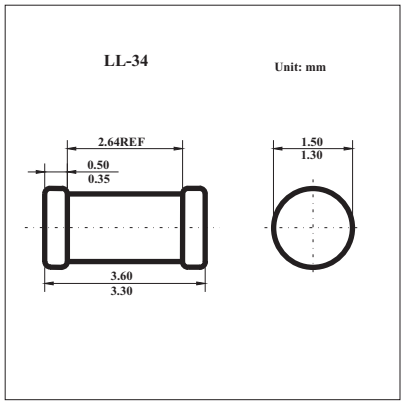
BA682; BA683



■ Features

- Continuous reverse voltage:max. 35 V
- Continuous forward current:max. 100 mA
- Low diode capacitance:max. 1.5 pF
- Low diode forward resistance:max. 0.7 to 1.2 Ω

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			35	V
Continuous forward current	I_F	single diode loaded		100	mA
Storage temperature	T_{stg}		-65	+150	℃
Junction temperature	T_j			150	℃
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}t\ p}$			300	K/W
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$			600	K/W

■ Electrical Characteristics Ta = 25℃

Parameter		Symbol	Conditions	Max	Unit
Forward voltage		V_F	I_F = 100 mA	1.0	V
Reverse current		I_R	V_R = 20 V	50	nA
			V_R = 20 V; T_j = 75 ℃	1	μA
Diode capacitance		C_d	f = 1 MHz; V_R = 1 V	1.5	pF
Diode capacitance	BA682	C_d	f = 1 MHz; V_R = 3 V	1.25	pF
	BA683			1.20	
Diode forward resistance	BA682	r_D	I_F = 3 mA; f = 200 MHz;	0.7	Ω
	BA683			1.2	
Diode forward resistance	BA682	r_D	I_F = 10 mA; f = 200 MHz;	0.5	Ω
	BA683			0.9	